

# GEORGE KONSTANTINIDIS

## LIST OF PUBLICATIONS



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Institute of Electronic Structure & Laser (IESL)  
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Heraklion Crete, Greece

December 2018

**[1]. PUBLISHED WORK (RESEARCHER ID: A-1719-2014)**

**[1]. Nanoarchitecture: Toward Quantum-Size Tuning of Superconductivity**

K.Y. Arutyunov, V. Zavialov, E.A Sedov, I.A Golokolenov, A.A. Zarudneva, I.N. Trun'kin, A. L. Vasiliev, G. Konstantinidis, A. Stavrinidis, G. Stavrinidis, M.D. Croitoru, A. A. Shanenko  
*Accepted at Phys. Status Solidi RRL*

**[2]. Cross-Section Doping Topography of 4H-SiC VJFETs by Various Techniques**

K.Tsagaraki, M. Nafouti, H. Peyre, K. Vamvoukakis, N. Makris, M. Kayambaki, A. Stavrinidis, G. Konstantinidis, M. Panagopoulou, D. Alquier, K. Zekentes  
*Materials Science Forum 924, pp. 653-656, Published: 2018*  
DOI: 10.4028/www.scientific.net/MSF.924.653

**[3]. A Continuous Semi-Empirical VJFET Capacitance Model from Sub to above Threshold Regime**

N. Makris, M. Kayambaki, A. Stavrinidis, G. Konstantinidis, G. Zekentes  
*Materials Science Forum 924, pp. 649-652, Published: 2018*  
DOI: 10.4028/www.scientific.net/MSF.924.649

**[4]. On the Optimum Determination and Use of SiC VJFET Threshold Voltage**

M. Kayambaki, N. Makris, A. Stavrinidis, G. Konstantinidis, G. Zekentes  
*Materials Science Forum 924, pp. 657-660, Published: 2018*  
DOI: 10.4028/www.scientific.net/MSF.924.65

**[5]. Channel width effect on the operation of 4H-SiC vertical JFETs**

K. Vamvoukakis, D. Stefanakis, S. Stavrinidis, K. Vassilevski, G. Konstantinidis, M. Kayambaki, K. Zekentes  
*PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, Volume: 214, Issue: 4, Article Number: 1600452, Published: APR 2017*  
DOI: 10.1002/pssa.201600452

**[6]. Electrical properties of SiNx films with embedded CNTs for MEMS capacitive switches**

M. Koutsourelis, G. Stavrinidis, D. Birpiliotis, G. Konstantinidis, G. Papaioannou  
*MICROELECTRONICS RELIABILITY, Volume: 76, pp: 614-618, Special Issue: SI, Published: SEP 2017*  
DOI: 10.1016/j.microrel.2017.07.041

**[7]. GaN Membrane Supported SAW Pressure Sensors With Embedded Temperature Sensing Capability**

Al. Muller, G. Konstantinidis, I. Giancu, GC. Adam, A. Stefanescu, G. Stavrinidis, A. Kostopoulos, G. Boldeiu, A. Dinescu  
*IEEE SENSORS JOURNAL, Volume: 17, Issue: 22, pp: 7383-7393, Published: NOV 15 2017*  
DOI: 10.1109/JSEN.2017.2757770

**[8]. Investigation of thin InN/GaN heterostructures with in situ SiNx dielectric grown by plasma-assisted molecular beam epitaxy**

C. Zervos, A. Adikimenakis, P. Beleniotis, A. Kostopoulos, M. Androulidaki, K. Tsagaraki, M. Kayambaki, G. Konstantinidis, A. Georgakilas  
*Journal of Vacuum Science & Technology B, Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena vol 35, 2, pp 021210, Published: 2017*  
DOI: 10.1116/1.4977606

**[9]. Response to comments on "GaN/Si based single SAW resonator temperature sensor operating in the GHz frequency range"**

Müller, A. Stefanescu, G. Konstantinidis  
*Sensors and Actuators A: Physical, vol 247, pp. 162–163, Published: 2016*  
DOI: 10.1016/j.sna.2016.05.047

**[10]. A computational platform for continuous seizure anticipation, monitoring and clinical evaluation**

- Giannakakis, G, Padiaditis, M, Stavrinidis, G.Konstantinidis, G.Kritsotakis, V. Tsakanikas, V. Ligerakis, M. Sakkalis, V.Vorgia, P.Tsiknakis  
*Studies in Health technology and informatics Vol. 224, 108, Published: 2016*  
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- [11]. **Study of the effect of the operating frequency of a GaN Lamb wave device to viscosity and protein sensing**  
A. Pantazis, G. Konstantinidis, E. Gizeli,  
*IEEE sensors Journal Vol.16, No.19, 7028, Published: 2016*  
DOI: 10.1109/JSEN.2016.2596904
- [12]. **Enhanced Stark tuning of single InAs (211)B quantum dots due to nonlinear piezoelectric effect in zinc-blende nanostructures**  
S. Germanis, C. Katsidis, S. Tsintzos, A. Stavrinidis, G. Konstantinidis, N. Florini, J. Kioseoglou, G.P. Dimitrakopoulos, Th. Kehagias, Z. Hatzopoulos, N.T. Pelekanos  
*Physical Review Applied 6, 014004, Published: 2016*  
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- [13]. **Selective area growth of GaN nanowires on SiO<sub>2</sub> masked Si (111) substrates**  
J. Kruse, L. Lymberakis, S. Eftychis, A. Adikimenakis, G. Doundoulakis, K. Tsagaraki, M. Androulidaki, A. Oziersky, P. Dimitrakis, V. Ioannou-Sougleridis, P. Normand, T. Koukoula, P. Komninou, G. Konstantinidis, A. Georgakilas  
*Journal of Applied Physics 119, 224305, Published: 2016*  
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- [14]. **In situ SiN<sub>x</sub>/InN structures for InN field-effect transistors**  
C. Zervos, A. Adikimenakis, P. Beleniotis, A. Kostopoulos, M. Kayambaki, K. Tsagaraki, G. Konstantinidis, A. Georgakilas.  
*Applied Physics Letters 108, 142102, Published: 2016*  
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- [15]. **Technology of integrated self-aligned E/D-mode n++GaN/InAlN/AlN/GaN MOS HEMTs for mixed signal electronics**  
Blaho M., Gregusova D., Hascik S., Seifertova A., Tapajna M., Soltys J., Satka A., Nagy L., Chvala A., Carlin J-f., Grandjean N., Konstantinidis G., Kuzmik J  
*Semiconductor Science and Technology 31, 06501, Published: 2016*  
DOI: 10.1088/0268-1242/31/6/065011
- [16]. **SU8 microneedles based dry electrodes for electroencephalogram**  
G. Stavrinidis, K. Michelakis, V. Kontomitrou, G. Giannakakis, M. Sevrisianos, G. Sevrisianos, N. Chaniotakis, Y. Alifragis, G. Konstantinidis  
*Microelectronic Engineering 159,, 114-120, Published:2016*  
DOI: 10.1016/j.mee.2016.02.062
- [17]. **Analysis of current instabilities of thin AlN/GaN/AlN double heterostructure high electron mobility transistors**  
Zervos, C., Adikimenakis, A, Bairamis, A., Kostopoulos, A., Kayambaki, M., Tsagaraki, K., Konstantinidis, G., Georgakilas, A.  
*Semiconductor Science and Technology 31, 065002, Published: 2016*  
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- [18]. **Free-Standing Gallium Nitride Membrane-Based Sensor for the Impedimetric Detection of Alcohols**  
Y. Alifragis, G. Roussos, A. Pantazis, G. Konstantinidis, N. Chaniotakis  
*Journal of Applied Physics 119, 074502, Published: 2016*  
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- [19]. **Influence of Au based metallization on the phase velocity of GaN on Si Surface Acoustic Wave resonators**

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Stefanescu A., Müller A., Giangu I., Dinescu A., Konstantinidis G.  
*IEEE Electron Device Letters, Published: 2016*  
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**[20]. A tunable microwave slot antenna based on graphene**

Dragoman M., Neculoiu D., Bunea A., Deligeorgis G., Aldrigo M., Vasilache D., Dinescu A., Konstantinidis G., Mencarelli D., Pierantoni L., Mondreanu M.  
*Applied Physics Letters Volume: 106 Issue: 15 Published: APR 13 2015*  
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**[21]. Sezawa Propagation Mode in GaN on Si Surface Acoustic Wave Type Temperature Sensor Structures Operating at GHz Frequencies**

Mueller A., Giangu I., Stavrinidis A., Stefanescu A., Stavrinidis G., Dinescu A., Konstantinidis G.  
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**[22]. Characterization of a GaN Lamb-Wave Sensor for Liquid-Based Mass Sensing Applications**

Pantazis A., Konstantinidis G., Gizeli E.  
*IEEE Sensors Journal Volume: 14 Issue: 3 Pages: 908-911 Published: MAR 2014*  
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**[23]. Comparative study of AlN dielectric films' electrical properties for MEMS capacitive switches**

Koutsourelis M., Adikimenakis A., Michalakis L., Papandreou E., Stavrinidis G., Konstantinidis G., Georgakilas A., Papaioannou G.  
*Microelectronic Engineering Volume: 130 Pages: 69-73 Published: NOV 2014*  
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**[24]. Electron density and currents of AlN/GaN high electron mobility transistors with thin GaN/AlN buffer layer**

Bairamis A., Zervos Ch., Adikimenakis A., Kostopoulos A., Kayambaki M., Tsagaraki K., Konstantinidis G., Georgakilas A.  
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**[25]. GaN/Si based single SAW resonator temperature sensor operating in the GHz frequency range**

Mueller A., Konstantinidis G., Buiculescu V., Dinescu A., Stavrinidis A., Stefanescu A., Stavrinidis G., Giangu I., Cismaru A., Modoveanu A.  
*Sensors and Actuators a-Physical Volume: 209 Pages: 115-123 Published: MAR 2014*  
DOI: 10.1016/j.sna.2014.01.028

**[26]. Quantum coherence in momentum space of light-matter condensates**

C. Anton, G. Tosi, M. D. Martin, Z. Hatzopoulos, G. Konstantinidis, P. S. Eldridge, P. G. Savvidis, C. Tejedor, L. Vina  
*Physical Review B Volume: 90 Issue: 8 Published: AUG 25 2014*  
DOI: 10.1103/PhysRevB.90.081407

**[27]. Electrically controlled strong coupling and polariton bistability in double quantum wells**

C. Coulson, G. Christmann, P. Cristofolini, C. Grossmann, J. J. Baumberg, S. I. Tsintzos, G. Konstantinidis, Z. Hatzopoulos, P. G. Savvidis  
*Physical Review B Volume: 87 Issue: 4 Published: JAN 2013*  
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**[28]. Enhancement of higher harmonics in graphene-based coupled coplanar line microwave multipliers**

M. Dragoman, A. Cismaru, A. Dinescu, D. Dragoman, G. Stavrinidis, G. Konstantinidis  
*Journal of Applied Physics Volume: 114 Issue: 15 Published: OCT 2013*  
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**[29]. Recombination dynamics in piezoelectric (2 1 1)B InAs quantum dots**

S. Germanis, A. Beveratos, K. Gauthron, A. Stavrinidis, G. Konstantinidis, Z. Hatzopoulos, N.T. Pelekanos  
*Microelectronic Engineering Volume: 112 Pages: 179-182 Published: DEC 2013*  
DOI: 10.1016/j.mee.2013.03.159

**[30]. Residual stress distribution and deflection analysis of very thin GaN membrane supported devices**

A. Cismaru, A. Müller, G. Konstantinidis, F. Comanescu, M. Purica, A. Stefanescu, A. Stavrinidis, A. Dinescu<sup>1</sup>, A. Moldoveanu  
*Journal of Micromechanics and Microengineering Volume: 23 Issue: 1 Published: JAN 2013*  
DOI: 10.1088/0960-1317/23/1/015010

**[31]. Coupling Quantum Tunneling with Cavity Photons**

P. Cristofolini, G. Christmann, S. I. Tsintzos, G. Deligeorgis, G. Konstantinidis, Z. Hatzopoulos, P. G. Savvidis, J. J. Baumberg  
*Science Volume: 336 Issue: 6082 Pages: 704-707 Published: MAY 11 2012*  
DOI: 10.1126/science.1219010

**[32]. Effect of boiling aqua regia on MOCVD and MBE p-type GaN surfaces and Cr/p-GaN interfaces**

F.G. Kalaitzakis, G. Konstantinidis, L. Sygellou, S. Kennou, S. Ladas, N.T. Pelekanos  
*Microelectronic Engineering Volume: 90 Pages: 115-117 Published: FEB 2012*  
DOI: 10.1016/j.mee.2011.04.066

**[33]. Fabrication issues of 4H-SiC Static Induction Transistors**

A. Stavrinidis, G. Konstantinidis, M. Kayambaki, F. Cayrel, D. Alquier, Z. Gao, K. Zekentes  
*Silicon Carbide and Related Materials 2011, Pts 1 and 2 Volume: 717-720 Pages: 1049-1052 Published: 2012*  
DOI: 10.4028/www.scientific.net/MSF.717-720.1049

**[34]. Flexible chiral metamaterials in the terahertz regime: a comparative study of various designs**

G. Kenanakis, R. Zhao, A. Stavrinidis, G. Konstantinidis, N. Katsarakis, M. Kafesaki, C. M. Soukoulis, E. N. Economou.  
*Optical Materials Express Volume: 2 Issue: 12 Pages: 1702-1712 Published: DEC 2012*  
DOI: <https://doi.org/10.1364/OME.2.001702>

**[35]. Front and backside-illuminated GaN/Si based metal-semiconductor-metal ultraviolet photodetectors manufactured using micromachining and nano-lithographic technologies**

A. Müller, G. Konstantinidis, M. Androulidaki, A. Dinescu, A. Stefanescu, A. Cismaru, D. Neculoiu, E. Pavelescu, A. Stavrinidis  
*Thin Solid Films Volume: 520 Issue: 6 Pages: 2158-2161 Published: JAN 2012*  
DOI: 10.1016/j.tsf.2011.09.045

**[36]. Graphene radio: Detecting radiowaves with a single atom sheet**

M. Dragoman, D. Neculoiu, A. Cismaru, G. Deligeorgis, G. Konstantinidis, D. Dragoman  
*Applied Physics Letters Volume: 101 Issue: 3 Published: JUL 2012*  
DOI: 10.1063/1.4738762

**[37]. Graphene-like metal-on-silicon field-effect transistor**

M. Dragoman, G. Konstantinidis, K. Tsagaraki, T. Kostopoulos, D. Dragoman, D. Neculoiu  
*Nanotechnology Volume: 23 Issue: 30 Published: AUG 3 2012*  
DOI: 10.1088/0957-4484/23/30/305201

**[38]. Millimeterwave Schottky diode on graphene monolayer via asymmetric metal contacts**

M. Dragoman, G. Deligeorgis, A. Muller, A. Cismaru, D. Neculoiu, G. Konstantinidis, D. Dragoman, A. Dinescu, F. Comanescu  
*Journal of Applied Physics Volume: 112 Issue: 8 Published: OCT 2012*  
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**[39]. Monolithic integration of nitride-based transistor with Light Emitting Diode for sensing applications**

F.G. Kalaitzakis, E. Iliopoulos, G. Konstantinidis, N.T. Pelekanos

**[40]. Radio frequency signal detection by ballistic transport in Y-shaped graphene nanoribbons**

G. Deligeorgis, F. Coccetti, G. Konstantinidis, R. Plana

*Applied Physics Letters Volume: 101 Issue: 1 Published: JUL 2012*

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**[41]. Self-powered microwave devices based on graphene ink decorated with gold nanoislands**

A. Radoi, M. Dragoman, A. Cismaru, G. Konstantinidis, D. Dragoman

*Journal of Applied Physics Volume: 112 Issue: 6 Published: SEP 15 2012*

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**[42]. Analysis of GaN Based SAW Resonators including FEM Modeling**

Stefanescu, A., Neculoiu, D., Mueller, A., A. Dinescu., G. Konstantinidis., A. Stavrinidis

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**[43]. Coplanar waveguide on graphene in the range 40 MHz-110 GHz**

M. Dragoman, D. Neculoiu, A. Cismaru, A. Muller, G. Deligeorgis, G. Konstantinidis, D. Dragoman, R. Plana

*Applied Physics Letters Volume: 99 Issue: 3 Published: JUL 2011*

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**[44]. Electrical behavior of multi-walled carbon nanotube network embedded in amorphous silicon nitride**

I. Stavarache, A. M. Lepadatu, V. S. Teodorescu, M. L. Ciurea, V. Iancu, M. Dragoman, G. Konstantinidis, R. Buiculescu

*Nanoscale Research Letters Volume: 6 Published: 2011*

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**[45]. A high frequency GaN Lamb-wave sensor device**

Pantazis, A., Gizeli, E., Konstantinidis, G.

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**[46]. Graphene for Microwaves**

M. Dragoman, D. Neculoiu, D. Dragoman, G. Deligeorgis, G. Konstantinidis, A. Cismaru, F. Coccetti, R. Plana

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**[47]. Interfacial polarisation on gallium arsenide membranes**

T. Prodromakis, G. Konstantinidis, C. Papavassiliou, C. Toumazou

*Micro & Nano Letters Volume: 5 Issue: 3 Pages: 178-180 Published: JUN 2010*

*DOI: 10.1049/mnl.2010.0008*

**[48]. MEMS Switch for 60 GHz Band**

D. Vasilache, G. Constantinidis, M. Dragoman, A. Takacs, F. Vladoianu, T. Kostopoulos, G. Boldeiu, V. Moagar, C. Tibeica, L. Bary, R. Plana, P. Schiopu, G. Caruntu

*Advanced Topics in Optoelectronics, Microelectronics, and Nanotechnologies V Volume: 7821 Published: 2010*

*DOI: 10.1117/12.881775*

**[49]. Microwave and millimeter wave devices based on micromachining of III-V semiconductors**

A. Müller, D. Neculoiu, G. Konstantinidis, T. Vähä-heikilä

*Advanced Materials and Technologies for Micro/nano-Devices, Sensors and Actuators Pages: 75-87 Published: 2010*

*DOI: 10.1007/978-90-481-3807-4\_6*

**[50]. Microwave switching of graphene field effect transistor at and far from the Dirac point**

G. Deligeorgis, M. Dragoman, D. Neculoiu, D. Dragoman, G. Konstantinidis, A. Cismaru, R. Plana  
*Applied Physics Letters* Volume: 96 Issue: 10 Published: MAR 2010  
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**[51]. Millimeter-wave generation via frequency multiplication in graphene**

M. Dragoman, D. Neculoiu, G. Deligeorgis, G. Konstantinidis, D. Dragoman, A. Cismaru, A. A. Muller, R. Plana  
*Applied Physics Letters* Volume: 97 Issue: 9 Published: AUG 2010  
DOI: 10.1063/1.3483872

**[52]. Negative differential resistance in GaN nanowire network**

M. Dragoman, G. Konstantinidis, A. Cismaru, D. Vasilache, A. Dinescu, D. Dragoman, D. Neculoiu, R. Buiculescu, G. Deligeorgis, A. P. Vajpeyi, A. Georgakilas  
*Applied Physics Letters* Volume: 96 Issue: 5 Published: FEB 2010  
DOI: 10.1063/1.3309670

**[53]. SAW Devices Manufactured on GaN/Si for Frequencies Beyond 5 GHz**

A. Mueller, D. Neculoiu, G. Konstantinidis, G. Deligeorgis, A. Dinescu, A. Stavrinidis, A. Cismaru, M. Dragoman, A. Stefanescu.  
*IEEE Electron Device Letters* Volume: 31 Issue: 12 Pages: 1398-1400 Published: DEC 2010  
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**[54]. 6.3-GHz Film Bulk Acoustic Resonator Structures Based on a Gallium Nitride/Silicon Thin Membrane**

A. Muller, D. Neculoiu, G. Konstantinidis, A. Stavrinidis, D. Vasilache, A. Cismaru, M. Danila, M. Dragoman, G. Deligeorgis, K. Tsagaraki  
*IEEE Electron Device Letters* Volume: 30 Issue: 8 Pages: 799-801 Published: AUG 2009  
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**[55]. AlN on silicon based surface acoustic wave resonators operating at 5 GHz**

D. Neculoiu, A. Muller, G. Deligeorgis, A. Dinescu, A. Stavrinidis, D. Vasilache, A.M. Cismaru, G.E. Stan, G. Konstantinidis  
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**[56]. Application of gold nanodots for Maxwell-Wagner loss reduction**

T. Prodromakis, C. Papavassiliou, G. Konstantinidis, C. Toumazou  
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**[57]. Current oscillations in a wide graphene sheet**

M. Dragoman, D. Dragoman, G. Deligiorgis, G. Konstantinidis, D. Neculoiu, A. Cismaru, R. Plana  
*Journal of Applied Physics* Volume: 106 Issue: 4 Published: AUG 15 2009  
DOI: 10.1063/1.3208061

**[58]. Fabrication and Characterization of Cr-based Schottky Diode on n-type 4H-SiC**

C. Koliakoudakis, J. Dontas, S. Karakalos, M. Kayambaki, S. Ladas, G. Konstantinidis, S. Kennou, K. Zekentes  
*Silicon Carbide and Related Materials 2008* Volume: 615-617 Pages: 651-654 Published: 2009  
DOI: 10.4028/www.scientific.net/MSF.615-617.651

**[59]. GaN membrane-supported UV photodetectors manufactured using nanolithographic processes**

A. Müller, G. Konstantinidis, M. Dragoman, D. Neculoiu, A. Dinescu, M. Androulidaki, M. Kayambaki, A. Stavrinidis, D. Vasilache, C. Buiculescu, I. Petrini, A. Kostopoulos, D. Dascalu.  
*Microelectronics Journal* Volume: 40 Issue: 2 Pages: 319-321 Published: FEB 2009  
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**[60]. High electron mobility transistors based on the AlN/GaN heterojunction**

A. Adikimenakis, K.E. Aretouli, E. Iliopoulos, A. Kostopoulos, K. Tsagaraki, G. Konstantinidis, A. Georgakilas

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**[61]. InAs nanostructures on polar GaAs surfaces**

G.E. Dialynas, A. Pantazis, Z. Hatzopoulos, M. Androulidaki, K. Tsagaraki, G. Konstantinidis, C. Xenogianni, E. Trichas, S. Tsintzos, P.G. Savvidis, N.T. Pelekanos

*International Journal of Nanotechnology* Volume: 6 Issue: 1-2 Pages: 124-136 Published: 2009

DOI: 10.1504/IJNT.2009.021712

**[62]. Microwave propagation in graphene**

G. Deligeorgis, M. Dragoman, D. Neculoiu, D. Dragoman, G. Konstantinidis, A. Cismaru, R. Plana

*Applied Physics Letters* Volume: 95 Issue: 7 Published: AUG 17 2009

DOI: 10.1063/1.3202413

**[63]. Rapid thermal annealing temperature dependence of noise properties in Au/n-GaAs Schottky diodes with embedded InAs quantum dots in asymmetric In<sub>0.2</sub>Ga<sub>0.8</sub>As wells**

N. Arpatzanis, N. A. Hastas, C. A. Dimitriadis, G. Konstantinidis, C. Charitidis, J. D. Song, W. J. Choi, J. I. Lee

*Physica Status Solidi B-Basic Solid State Physics* Volume: 246 Issue: 4 Pages: 880-884 Published: APR 2009

DOI: 10.1002/pssb.200880580

**[64]. A GaAs polariton light-emitting diode operating near room temperature**

S. I. Tsintzos, N. T. Pelekanos, G. Konstantinidis, Z. Hatzopoulos, P. G. Savvidis

*Nature* Volume: 453 Issue: 7193 Pages: 372-375 Published: MAY 15 2008

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**[65]. Anti-binding of biexcitons in (211)B InAs/GaAs piezoelectric quantum dots**

G.E. Dialynas, C. Xenogianni, S. Tsintzos, E. Trichas, P.G. Savvidis, G. Konstantinidis, J. Renard, B. Gayral, Z. Hatzopoulos, N.T. Pelekanos

*Physica E-Low-Dimensional Systems & Nanostructures* Volume: 40 Issue: 6 Pages: 2113-2115 Published: APR 2008

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**[66]. Cr/4H-SiC Schottky contacts investigated by electrical and photoelectron spectroscopy techniques**

C. Koliakoudakis<sup>1</sup>, J. Dontas, S. Karakalos, M. Kayambaki, S. Ladas, G. Konstantinidis, K. Zekentes, S. Kennou

*Physica Status Solidi a-Applications and Materials Science* Volume: 205 Issue: 11 Pages: 2536-2540 Published: NOV 2008

DOI: 10.1002/pssa.200780212

**[67]. Dielectric charging effect estimation to MIM structured RF MEMS devices due to 1 MeV gamma-ray photons irradiation**

V. Theonas, G. Papaioannou, G. Konstantinidis, J. Papapolumerou

*Physica Status Solidi C - Current Topics in Solid State Physics, Vol 5, No 12 2008* Volume: 5 Issue: 12 Pages: 3850-3853 Published: 2008

DOI: 10.1002/pssc.200780186

**[68]. Estimation of metallic contact effects on the performance of (SI) GaAs soft X-ray radiation detectors**

V. Theonas, G. Papaioannou, G. Konstantinidis, J. Papapolumerou

*Physica Status Solidi C - Current Topics in Solid State Physics, Vol 5, No 12 2008* Volume: 5 Issue: 12 Pages: 3638-3642 Published: 2008

DOI: 10.1002/pssc.200780216

**[69]. GaN membrane metal-semiconductor-metal ultraviolet photodetector**



A. Müller, G. Konstantinidis, M. Dragoman, D. Neculoiu, A. Kostopoulos, M. Androulidaki, M. Kayambaki, D. Vasilache.

*Applied Optics* Volume: 47 Issue: 10 Pages: 1453-1456 Published: APR 2008

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